

HIGH K DIELECTRIC FILM AND METHOD FOR MAKING

Abstract

A dielectric layer comprises lanthanum, aluminum, nitrogen, and oxygen
5 and is formed between two conductors or a conductor and substrate. In one
embodiment, the dielectric layer is graded with among the lanthanum, nitrogen,
or aluminum. An additional insulating layer may be formed between the
conductor or substrate and the dielectric layer. The dielectric layer can be
formed by atomic layer chemical vapor deposition, physical vapor deposition,
10 organometallic chemical vapor deposition or pulsed laser deposition.

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